

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: SQA444CEJW-T1_GE3
Manufacturer: Vishay Siliconix
Package: Please confirm with sales
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-siliconix/sqa444cejw-t1-ge3.html>

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Contact Information

Email: info@antrexco.com

WhatsApp: +86-186-8066-5326

Website: <https://antrexco.com>

Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

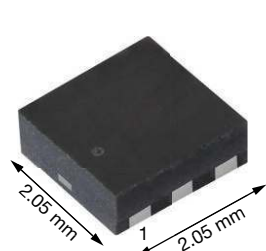
Secure sourcing support for OEM / EMS projects

Note:

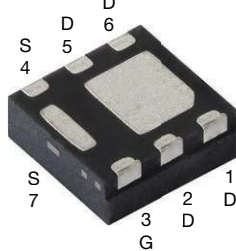
This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PowerPAK® SC-70W-6L Single


Top View



Bottom View

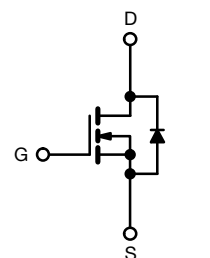
Marking Code: Q9XXXX

PRODUCT SUMMARY

V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0390
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0526
I_D (A)	9
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQA444CEJW (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current	I_D	$T_C = 25$ °C ^a	9
		$T_C = 125$ °C	7.7
Continuous source current (diode conduction) ^a	I_S	9	A
Pulsed drain current ^b	I_{DM}	28	A
Single pulse avalanche current	I_{AS}	12.5	A
Single pulse avalanche energy	E_{AS}	7.81	mJ
Maximum power dissipation	P_D	$T_C = 25$ °C	13.6
		$T_C = 125$ °C	4.5
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	90	°C/W
Junction-to-case (drain)	R_{thJC}	11	°C/W

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

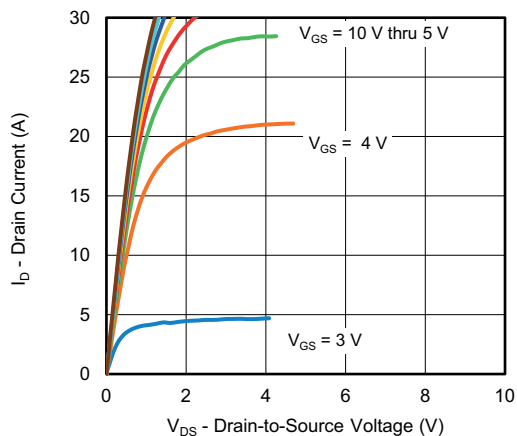
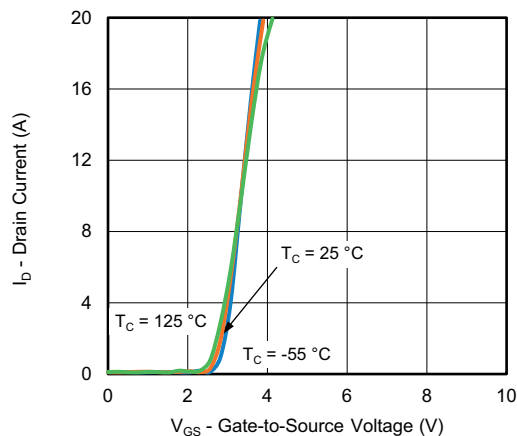
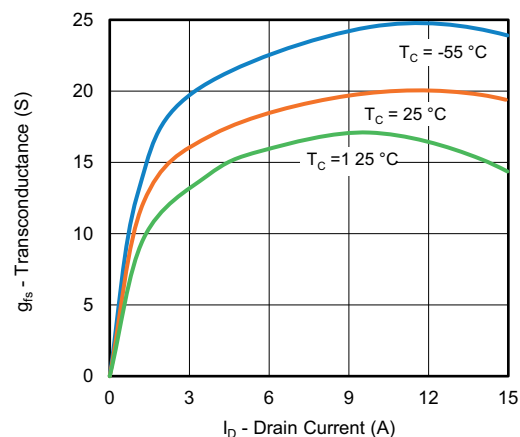
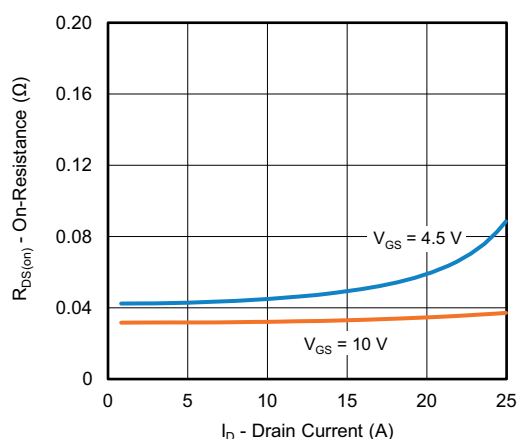
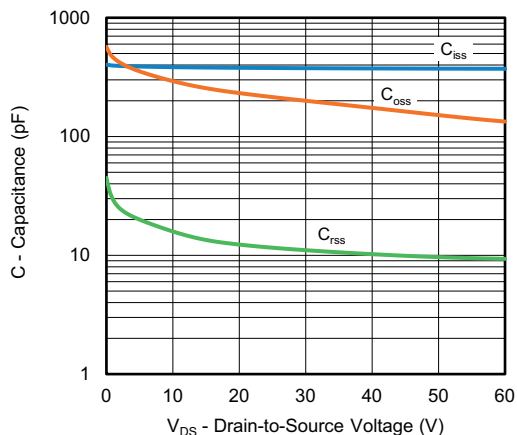
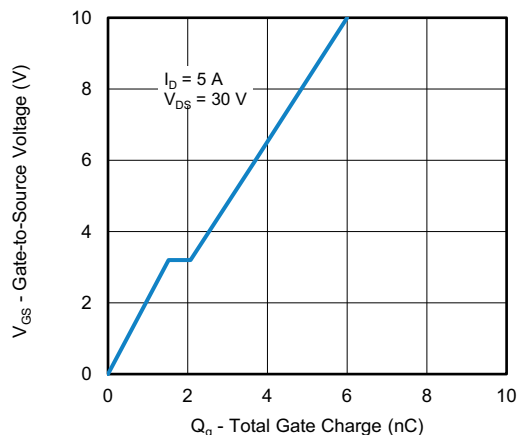


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.5 A	-	0.0318	0.0390	Ω
		V _{GS} = 10 V	I _D = 4.5 A, T _J = 125 °C	-	-	0.0623	
		V _{GS} = 10 V	I _D = 4.5 A, T _J = 175 °C	-	-	0.0764	
		V _{GS} = 4.5 V	I _D = 3 A	-	0.0429	0.0526	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 4.5 A		-	17	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	378	530	pF
Output capacitance	C _{oss}			-	215	300	
Reverse transfer capacitance	C _{rss}			-	12	17	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 5 A	-	6	9	nC
Gate-source charge ^c	Q _{gs}			-	1.52	-	
Gate-drain charge ^c	Q _{gd}			-	0.55	-	
Gate resistance	R _g	f = 1 MHz		0.225	0.450	0.675	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 6 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω		-	8	12	ns
Rise time ^c	t _r			-	3	6	
Turn-off delay time ^c	t _{d(off)}			-	13	20	
Fall time ^c	t _f			-	3	6	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	28	A
Forward voltage	V _{SD}	I _F = 4.5 A, V _{GS} = 0 V		-	0.84	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs		-	16	32	ns
Body diode reverse recovery charge	Q _{rr}			-	8.4	17	nC
Reverse recovery fall time	t _a			-	9	-	ns
Reverse recovery rise time	t _b			-	7	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.0	-	A

Notes

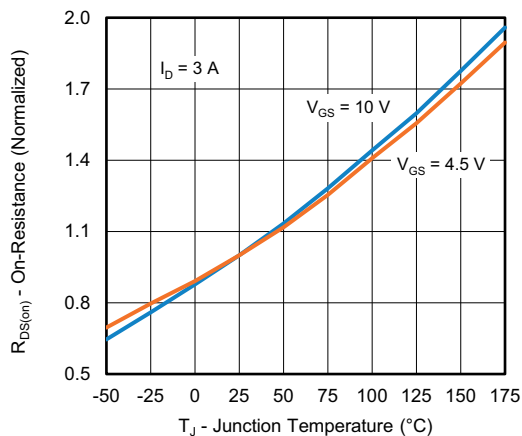
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

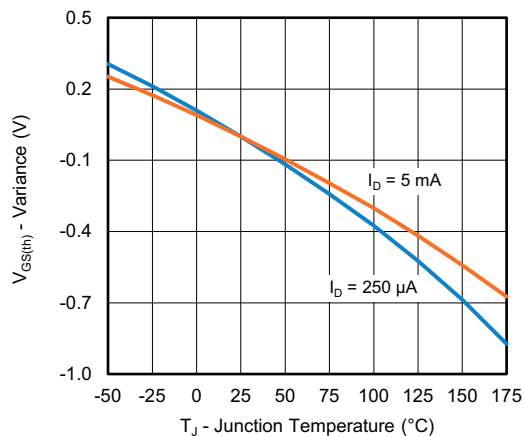
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge



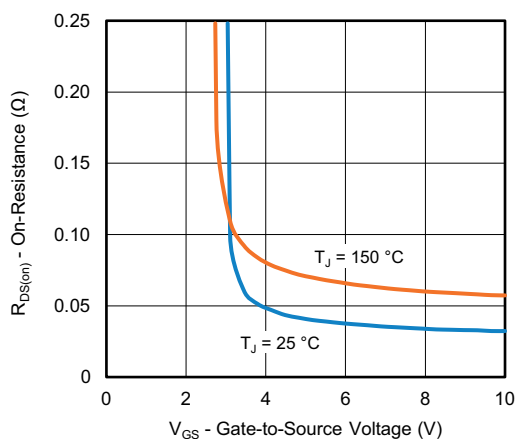
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



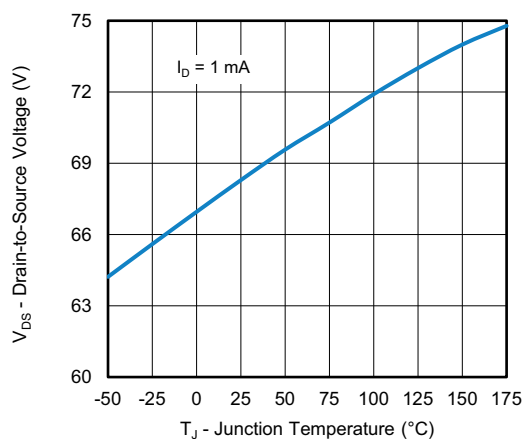
On-Resistance vs. Junction Temperature



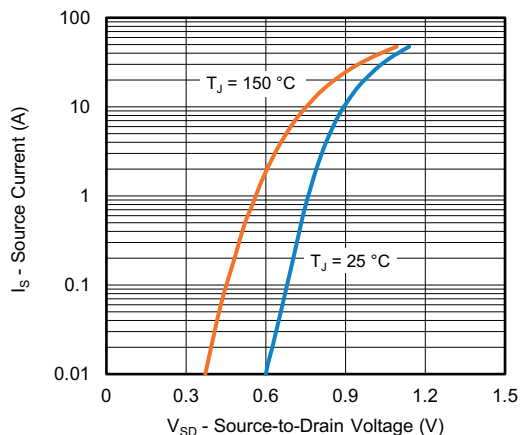
Threshold Voltage



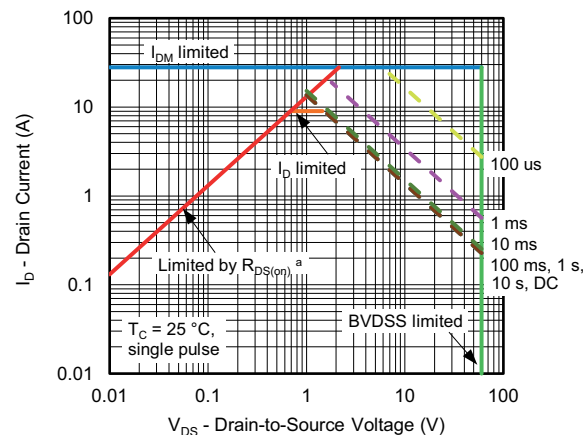
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



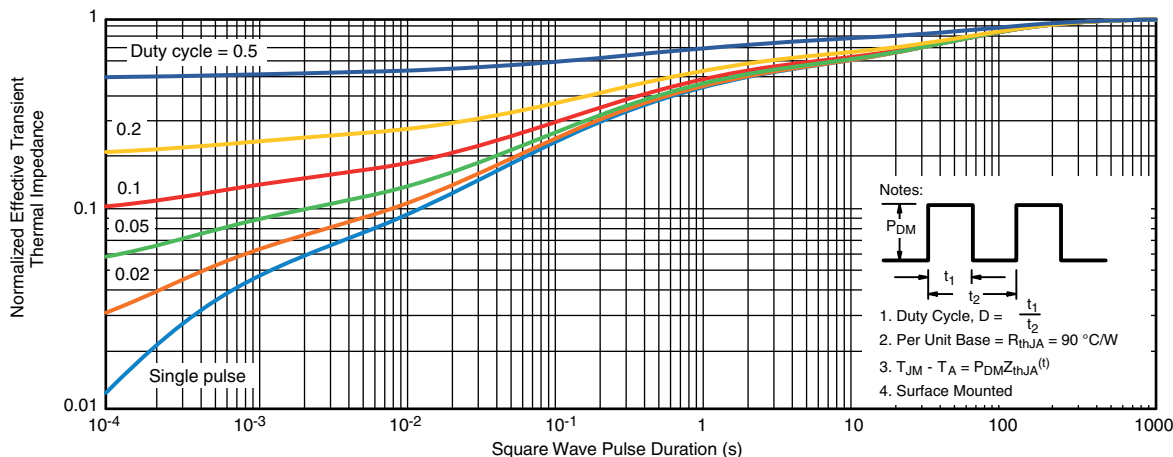
Source Drain Diode Forward Voltage



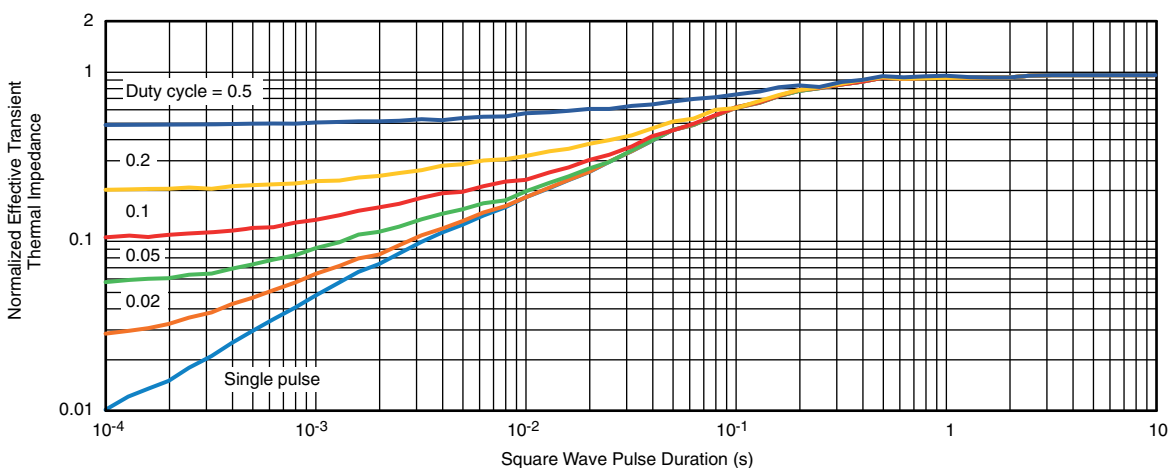
Safe Operating Area



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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